

Title (en)

FLASH MEMORY SYSTEM, AND METHODS OF CONSTRUCTING AND UTILIZING SAME.

Title (de)

FLASH-SPEICHERSYSTEM-UND VERFAHREN ZUR HERSTELLUNG UND ZUR VERWENDUNG DESSELBEN.

Title (fr)

SYSTEME DE MEMOIRE FLASH ET SES PROCEDES DE CONSTRUCTION ET D'UTILISATION.

Publication

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Application

EP 94900481 A 19931102

Priority

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Abstract (en)

[origin: WO9410686A1] An N-channel SNOS or SONOS type memory array (100) has programmable memory states with a negative, depletion mode threshold lower in magnitude than the supply voltage VCC when erased and a positive threshold when programmed. During reading, the supply voltage VCC is applied to the drain (16), while a positive voltage VR less than VCC-Vds,sat is applied to the source (14), where Vds,sat is the saturation voltage of the device. A reference voltage may also be applied to the substrate (11) during a read operation. Selected devices have VR applied to the gate (12), while inhibited devices have ground or the substrate potential VSS applied to the gate (12).

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